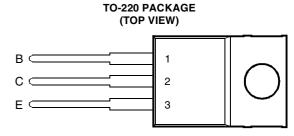


- Designed for Complementary Use with BDW23, BDW23A, BDW23B and BDW23C
- 50 W at 25°C Case Temperature
- 6 A Continuous Collector Current
- Minimum h<sub>FE</sub> of 750 at 2 A, 3 V



Pin 2 is in electrical contact with the mounting base.

MDTRACA

# This series is currently available, but not recommended for new designs.

### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BDW24		-45		
Collector-base voltage ( $I_E = 0$ )	BDW24A	V	-60	v	
Collector base voltage (iE = 0)	BDW24B	V <sub>CBO</sub>	-80	V	
	BDW24C		-100		
	BDW24		-45		
Collector-emitter voltage (I <sub>B</sub> = 0)	BDW24A	V	-60	V	
	BDW24B	V <sub>CEO</sub>	-80		
	BDW24C		-100		
Emitter-base voltage	V <sub>EBO</sub>	-5	V		
Continuous collector current	I <sub>C</sub>	-6	Α		
Continuous base current	I <sub>B</sub>	-0.2	Α		
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)	P <sub>tot</sub>	50	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note 2)			2	W	
Operating junction temperature range	T <sub>j</sub>	-65 to +150	°C		
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C		
Operating free-air temperature range	T <sub>A</sub>	-65 to +150	°C		

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.

2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.



# electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS				MIN	TYP	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> = -100 mA	I <sub>B</sub> = 0	(see Note 3)	BDW24 BDW24A BDW24B BDW24C	-45 -60 -80 -100			V
I <sub>CEO</sub>	Collector-emitter cut-off current	~-	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BDW24 BDW24A BDW24B BDW24C			-0.5 -0.5 -0.5 -0.5	mA
І <sub>СВО</sub>	Collector cut-off current	~ -	_		BDW24 BDW24A BDW24B BDW24C			-0.2 -0.2 -0.2 -0.2	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = -5 V	I <sub>C</sub> = 0					-2	mA
h <sub>FE</sub>	Forward current transfer ratio	$V_{CE} = -3 V$ $V_{CE} = -3 V$ $V_{CE} = -3 V$	$I_C = -2 A$	(see Notes 3 and	4)	1000 750 100		20000	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	$I_B = -8 \text{ mA}$ $I_B = -60 \text{ mA}$	-	(see Notes 3 and	14)			-2 -3	٧
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>B</sub> = -8 mA	I <sub>C</sub> = -2 A	(see Notes 3 and	14)			-2.5	٧
V <sub>BE(on)</sub>	Base-emitter voltage	$V_{CE} = -3 V$ $V_{CE} = -3 V$	$I_C = -1 A$ $I_C = -6 A$	(see Notes 3 and	14)			-2.5 -3	٧
V <sub>EC</sub>	Parallel diode forward voltage	I <sub>E</sub> = -2 A	I <sub>B</sub> = 0					-1.8	V

NOTES: 3. These parameters must be measured using pulse techniques,  $t_p$  = 300  $\mu$ s, duty cycle  $\leq$  2%.

#### thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			2.5	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

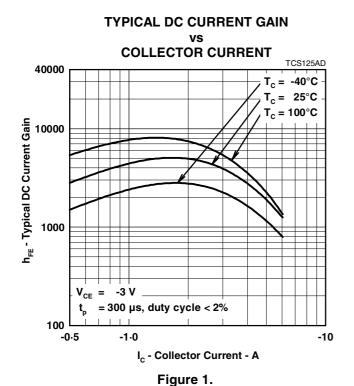
## resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t <sub>on</sub>	Turn-on time	I <sub>C</sub> = -3 A	$I_{B(on)} = -12 \text{ mA}$	$I_{B(off)} = 12 \text{ mA}$		1		μs
t <sub>off</sub>	Turn-off time	$V_{BE(off)} = 4.5 V$	$R_L = 10 \Omega$	$t_p = 20 \mu s, dc \le 2\%$		5		μs

<sup>&</sup>lt;sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

<sup>4.</sup> These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

#### **TYPICAL CHARACTERISTICS**



**COLLECTOR-EMITTER SATURATION VOLTAGE** 

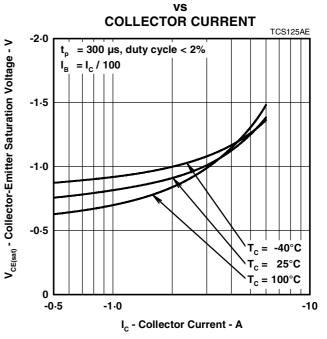
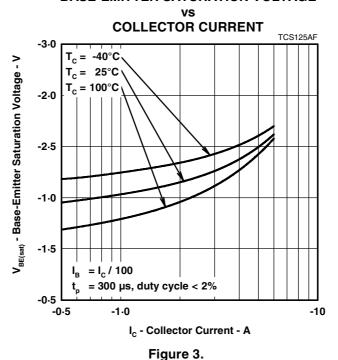


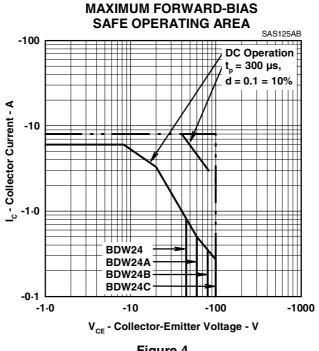
Figure 2.

#### **BASE-EMITTER SATURATION VOLTAGE**



#### PRODUCT INFORMATION

#### **MAXIMUM SAFE OPERATING REGIONS**



#### Figure 4.

#### THERMAL INFORMATION

# **MAXIMUM POWER DISSIPATION**

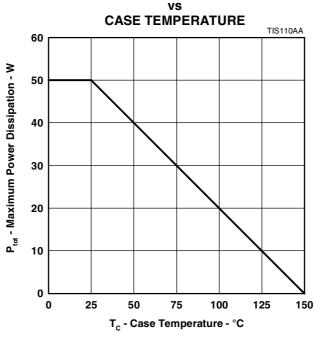


Figure 5.